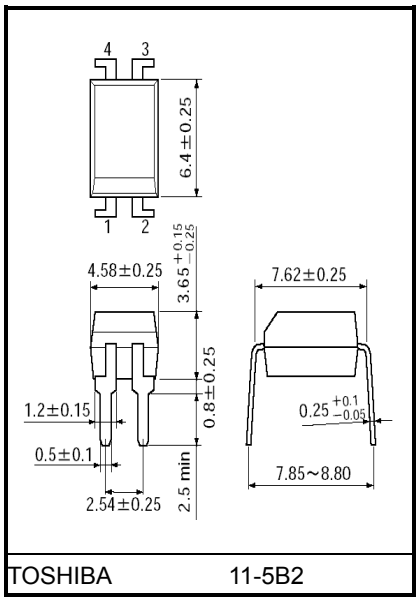
Tentative

TOSHIBA Photocoupler GaAs IRED & PHOTO-TRIAC

TLP363J

Unit: mm



TOSHIBA 11-5B2

Weight: 0.26 g

Triac Drivers

Programmable Controllers

AC-Output Modules

Solid State Relays

The TOSHIBA TLP363J consists of a zero-voltage-crossing turn-on photo-triac optically coupled to a gallium-arsenide infrared-emitting diode in a four-lead plastic DIP package.
This product has a greater capacity to withstand external noise than the TLP361J.

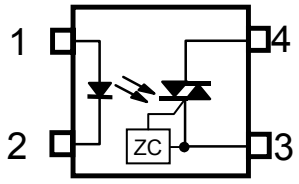
- Peak Off-State Voltage : 600 V (Min)
- Trigger LED Current : 10 mA (Max)
- On-State Current : 100 mA (Max)
- Isolation Voltage : 5000 Vrms (Min)
- Zero Crossing Function
- UL-Recognized : UL1577、file No.E67349
- Option (D4) type
  TÜV approved : DIN EN60747-5-2
  Certificate No. R50033433
  Maximum Operating Insulation Voltage : 890 Vpk
  Maximum Permissible Overvoltage : 8000 Vpk

(Note) When an EN60747-5-2 approved type is needed, please designate “Option (D4).”

•Construction Mechanical Rating

	7.62 mm pitch TLPXXX type	10.16 mm pitch TLPXXX type
Creepage Distance	7.0 mm (Min)	8.0 mm (Min)
Clearance	7.0 mm (Min)	8.0 mm (Min)
Insulation Thickness	0.4 mm (Min)	0.4 mm (Min)

PIN CONFIGURATION (TOP VIEW)



1: ANODE
2: CATHODE
3: TERMINAL1
4: TERMINAL2

•Trigger LED Current

Classification*	Trigger LED Current (mA) V_T = 3 V, Ta = 25°C		Marking of Classification
	Min.	Max.	
Standard	—	10	blank

(Note) When specifying the application type name for certification testing, be sure to use the standard product type name, e.g.,
TLP363J

Maximum Ratings (Ta=25°C)

CHARACTERISTIC			SYMBOL	RATING	UNIT
LED	Forward Current		I_F	50	mA
	Forward Current Derating (Ta ≥ 53°C)		ΔI_F /°C	−0.7	mA /°C
	Peak Forward Current (100 μs pulse, 100 pps)		I_{FP}	1	A
	Reverse Voltage		V_R	5	V
	Junction Temperature		T_j	125	°C
DETECTOR	Off-State Output Terminal Voltage		V_{DRM}	600	V
	On-State RMS Current	Ta = 25°C	$I_{T(RMS)}$	100	mA
		Ta = 70°C		50	
	On-State Current Derating (Ta ≥ 25°C)		ΔI_T/°C	-1.1	mA /°C
	Peak On-State Current (100 μs pulse, 120 pps)		I_{TP}	2	A
	Peak Nonrepetitive Surge Current (Pw =10 ms, DC = 10%)		I_{TSM}	1.2	A
	Junction Temperature		T_j	115	°C
Storage Temperature Range			T_{stg}	−55~125	°C
Operating Temperature Range			T_{opr}	−40~100	°C
Lead Soldering Temperature (10 s)			T_{sol}	260	°C
Isolation Voltage (AC,1min. , R.H. ≤ 60%) (Note 1)			BV_S	5000	Vrms

(Note 1): Pins 1 and 2 are shorted together and pins 3 and 4 are shorted together.

Recommended Operating Conditions

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V_{AC}	—	—	240	V_{ac}
Forward Current	I_F	15	20	25	mA
Peak On-State Current	I_{TP}	—	—	1	A
Operating Temperature	T_{opr}	−25	—	85	°C

Electrical Characteristics (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	I_F = 10 mA	1.0	1.15	1.3	V
	Reverse Current	I_R	V_R = 5 V	—	—	10	μA
	Capacitance	C_T	V = 0, f = 1 MHz	—	30	—	pF
DETECTOR	Peak Off-State Current	I_{DRM}	V_{DRM} = 600 V	—	10	1000	nA
	Peak On-State Voltage	V_{TM}	I_{TM} = 100 mA	—	1.7	3.0	V
	Holding Current	I_H	—	—	0.6	—	mA
	Critical Rate of Rise of Off-State Voltage	dv/dt	Vin = 240 Vrms , Ta = 85°C (Note 2)	200	500	—	V/μs
	Critical Rate of Rise of Commutating Voltage	dv/dt(c)	Vin = 60 Vrms , I_T = 15 mA (Note 2)	—	0.2	—	V/μs

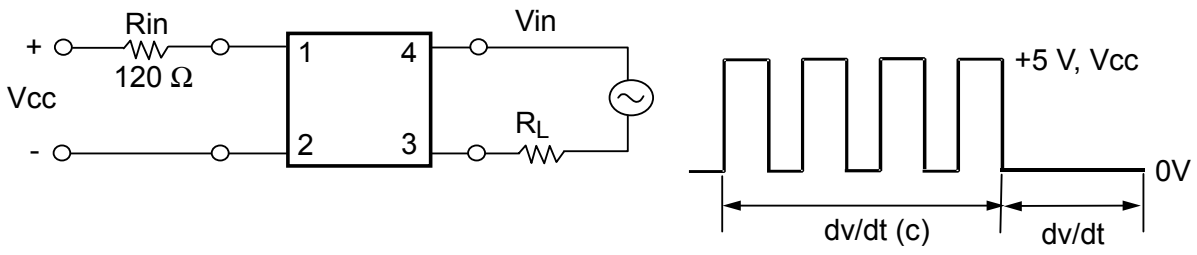
Coupled Electrical Characteristics (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Trigger LED Current	I_{FT}	V_T = 3 V	—	—	10	mA
Inhibit Voltage	V_{IH}	I_F = Rated I_{FT}	—	—	20	V
Leakage in Inhibited State	I_{IH}	I_F = Rated I_{FT} V_T = Rated V_{DRM}	—	200	600	μA
Turn-on Time	t_{ON}	V_D =3 → 1.5 V , R_L = 20 Ω I_F = Rated I_{FT}X1.5	—	30	100	μs
Impulse Noise Durability	V_N	t_N=1μs, Snuber condition 100 Ω +0.033 μF (Note.3)	—	2000	—	V

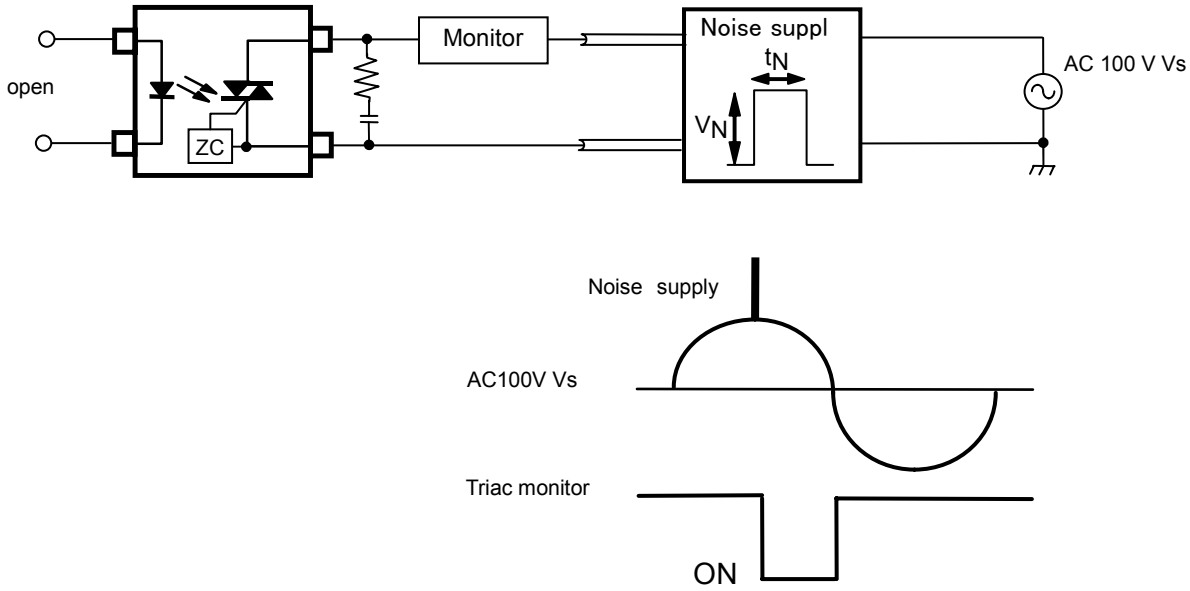
Isolation Characteristics (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	C_S	V_S = 0 , f = 1 MHz	—	0.8	—	pF
Isolation Resistance	R_S	V_S = 500 V, R.H.≤ 60%	1×10^{12}	10^{14}	—	Ω
Isolation Voltage	BV_S	AC , 1 minute	5000	—	—	Vrms
		AC , 1 second, in oil	—	10000	—	
		DC , 1 minute, in oil	—	10000	—	Vdc

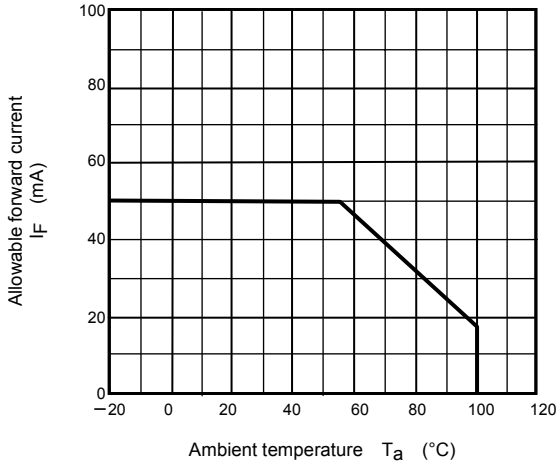
(Note 2): dv/dt TEST CIRCUIT



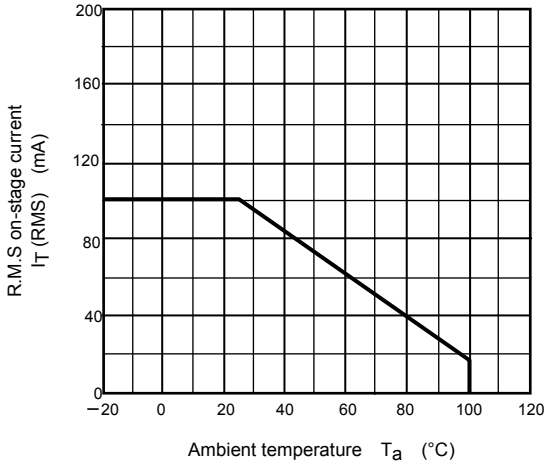
(Note 3): In-pulse noise durability test circuit



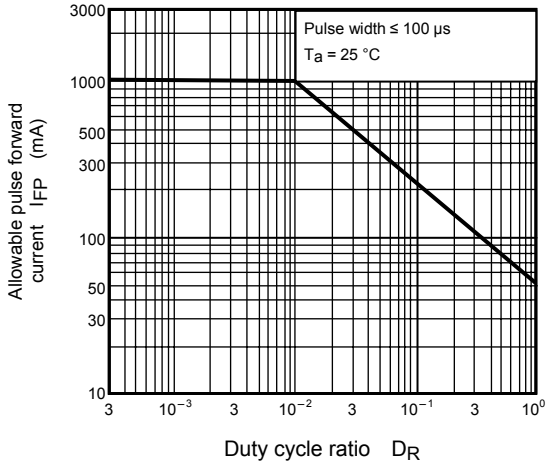
$I_F - T_a$



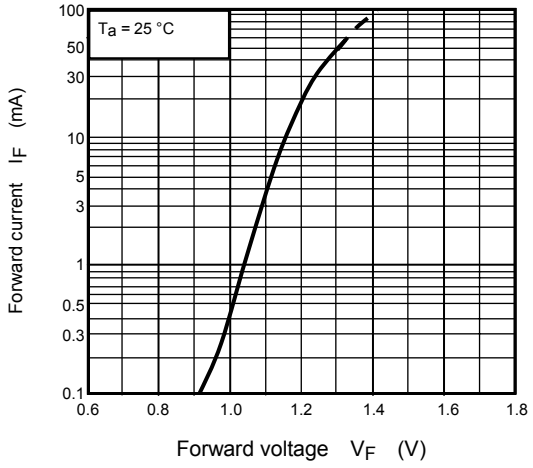
I_T (RMS) – T_a



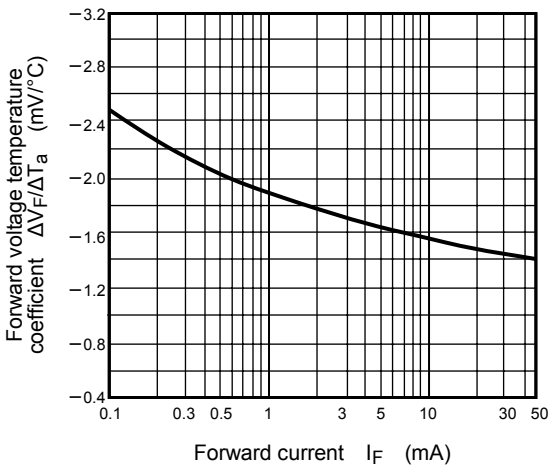
$I_{FP} - D_R$



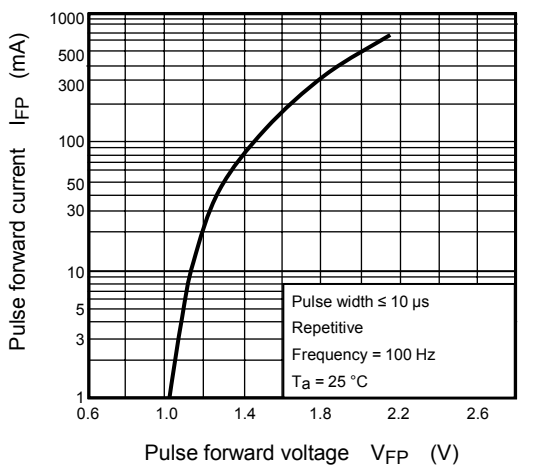
$I_F - V_F$



$\Delta V_F/\Delta T_a - I_F$

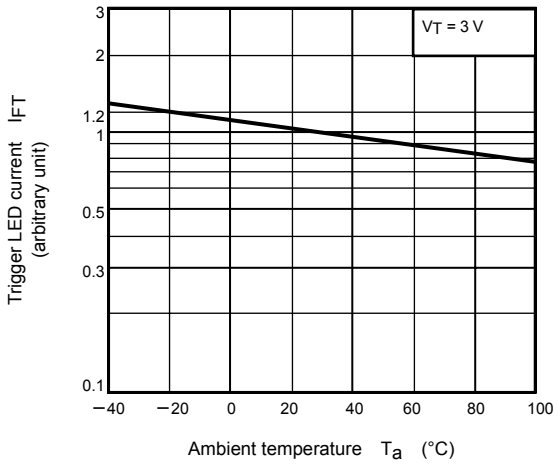


$I_{FP} - V_{FP}$

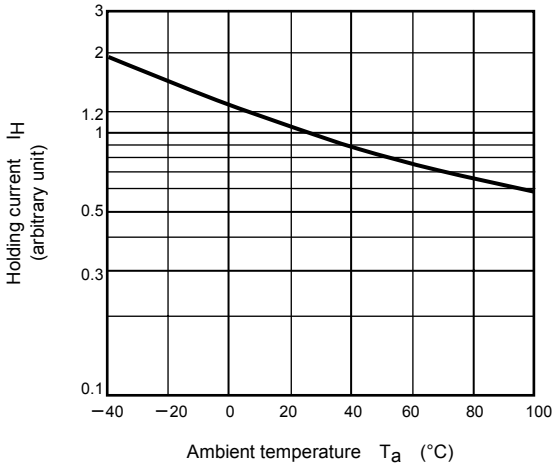


*: The above graphs show typical characteristics.

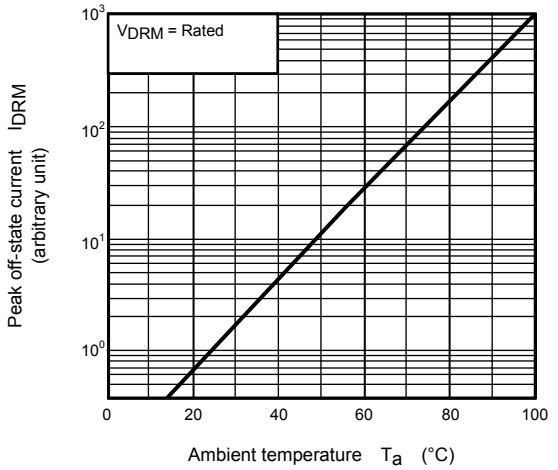
Normalized $I_{FT} - T_a$



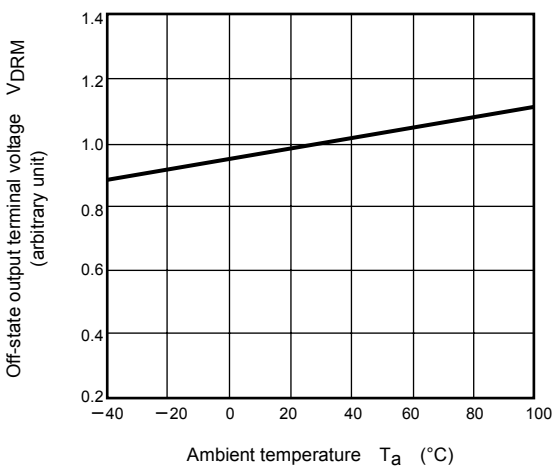
Normalized $I_H - T_a$



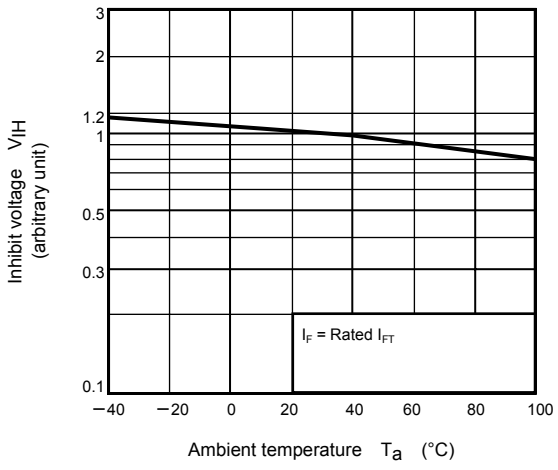
Normalized $I_{DRM} - T_a$



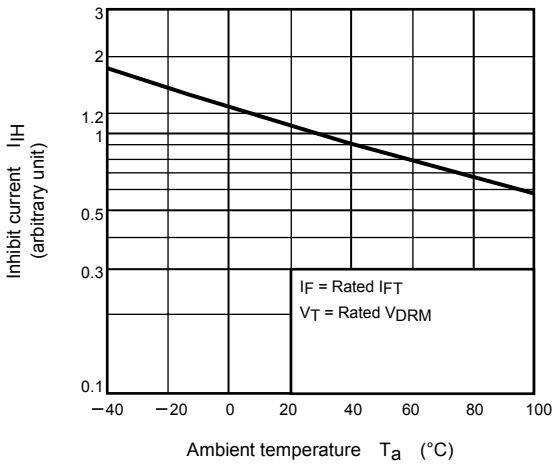
Normalized $V_{DRM} - T_a$



Normalized $V_{IH} - T_a$



Normalized $I_{IH} - T_a$



*: The above graphs show typical characteristics.

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